Silicon PNP transistor epitaxial type
6A882

[Applications]

General purpose amplifier and switching

[Feature]

High speed switching similar to MMBT3906

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-40	V
Collector-emitter voltage	VCEO	-40	V
Emitter-base voltage	VEBO	-6	V
Collector current	IC	-200	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-40	-	-	V	IC= -10uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-40	-	-	V	IC= -1mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-6	-	-	V	IE= -10uA, IC= 0A
Collector cut-off current	ICEX	-	-	-50	nA	VCE= -30V, VEB= -3V
Emitter cut-off current	IEBO	-	-	-50	nA	VEB= -5
DC current gain 1	hFE 1	60	-	-	-	VCE= -1V, IC= -0.1mA
DC current gain 2	hFE 2	80	-	-	-	VCE= -1V, IC= -1mA
DC current gain 3	hFE 3	100	-	300	-	VCE= -1V, IC= -10mA
DC current gain 4	hFE 4	60	-	-	-	VCE= -1V, IC= -50mA
DC current gain 5	hFE 5	30	-	-	-	VCE= -1V, IC= -100mA
Collector-emitter saturation voltage 1	VCE(sat) 1	-	-	-0.25	V	IC= -10mA, IB= -1mA
Collector-emitter saturation voltage 2	VCE(sat) 2	-	-	-0.4	V	IC= -50mA, IB= -5mA
Base-emitter saturation voltage 1	VBE(sat) 1	-0.65	-	-0.85	V	IC= -10mA, IB= -1mA
Base-emitter saturation voltage 2	VBE(sat) 2	-	-	-0.95	V	IC= -50mA, IB= -5mA
Transition frequency	f T	250	-	-	MHz	VCE= -20V, IE= 10mA
Output capacitance	Cob	-	-	4.5	pF	VCB= -5V, f = 1MHz, IE= 0A
Input capacitance	Cib	-	-	10	pF	VEB= -0.5V, f = 1MHz, IE= 0A
Delay Time	td	-	-	35	ns	VCC=-3V, VBE=0.5V
Rise Time	tr	-	-	35	ns	IC=-10mA, IB1=-1mA
Storage Time	ts	-	-	225	ns	VCC=-3V, IC=-10mA
Fall Time	tf	-	-	75	ns	IB1= -IB2=-1mA

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

Fig.1 hFE - IC
at VCE= -1V, Ta= 25C

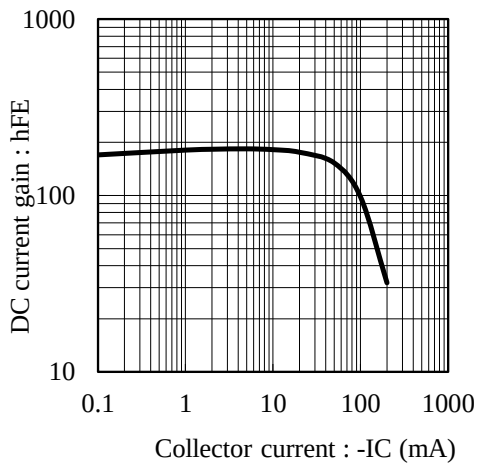

Fig.2 VCE(sat) - IC
at IC/IB= 10, Ta= 25C

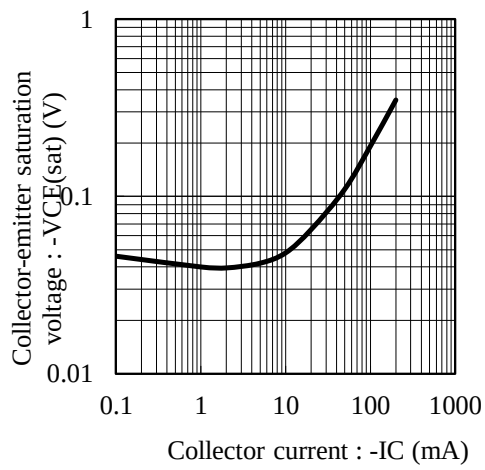

Fig.3 VBE(sat) - IC
at IC/IB= 10, Ta= 25C

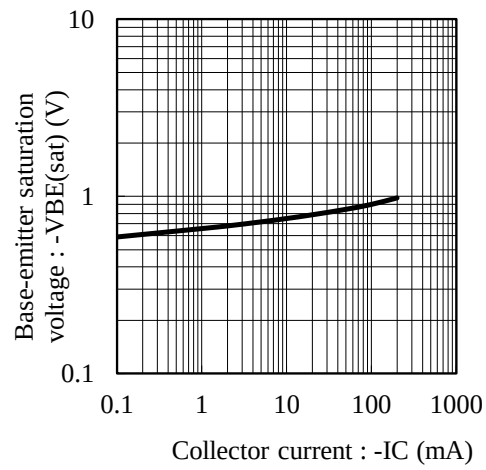

Fig.4 fT - IE
at VCE= -20V, Ta= 25C

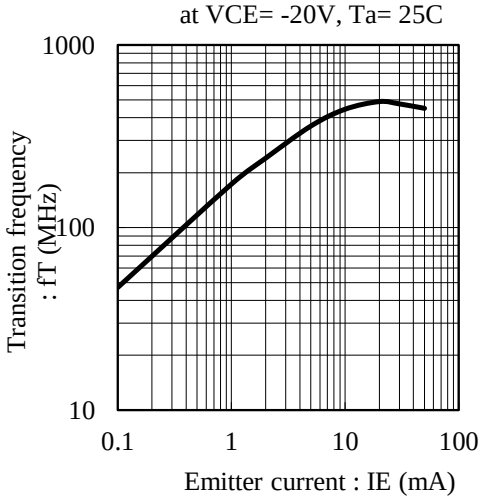

Fig.5 Cob - VCB
at f= 1MHz, Ta= 25C

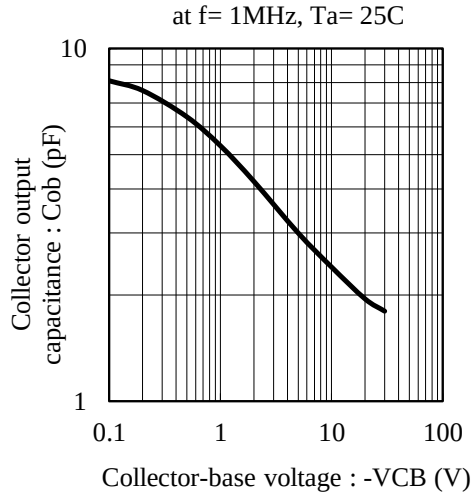

Fig.6 Cib - VEB
at f= 1MHz, Ta= 25C